

1.	Record Nr.	UNISALENTO991003916799707536
	Autore	Fogazzaro, Antonio
	Titolo	Piccolo mondo moderno
	Pubbl/distr/stampa	Milano : Hoepli, s.d.
	Descrizione fisica	461 p. ; 19 cm.
	Lingua di pubblicazione	Italiano
	Formato	Materiale a stampa
	Livello bibliografico	Monografia
2.	Record Nr.	UNINA9910712096703321
	Titolo	Conducting technical systems audits of ambient air monitoring programs : quality assurance guidance document
	Pubbl/distr/stampa	[Research Triangle Park], NC : , : U.S. Environmental Protection Agency, Office of Air Quality Planning and Standards, Air Quality Assessment Division, , 2017
	Descrizione fisica	1 online resource (199 unnumbered pages) : illustrations (some color), forms
	Soggetti	Air - Pollution - United States - Measurement Air quality - Standards - United States Air quality - United States Air quality monitoring stations - United States
	Lingua di pubblicazione	Inglese
	Formato	Materiale a stampa
	Livello bibliografico	Monografia
	Note generali	"November 2017." "EPA-454/B-17-004."
	Nota di bibliografia	Includes bibliographical references.

3. Record Nr.	UNINA9911006734003321
Autore	Riccio Michele
Titolo	Processing and Characteristics of Solid-State Structures
Pubbl/distr/stampa	Zurich : , : Trans Tech Publications, Limited, , 2024 ©2024
ISBN	9783036416465 3036416463
Edizione	[1st ed.]
Descrizione fisica	1 online resource (143 pages)
Collana	Solid State Phenomena, , 1662-9779 ; ; Volume 358
Altri autori (Persone)	IraceAndrea BreglioGiovanni
Soggetti	Metal oxide semiconductors Silicon carbide
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di contenuto	Intro -- Processing and Characteristics of Solid-State Structures -- Preface -- Table of Contents -- Investigation of Potential Impact of Nitridation Process on Single Event Gate Rupture Tolerance in SiC MOS Capacitors -- Venus Surface Environmental Chamber Test of SiC JFET-R Multi-Chip Circuit Board -- Coupled Non-Destructive Methods, Kelvin Force Probe Microscopy and μ -Raman to Characterize Doping in 4H-SiC Power Devices -- Concept and Technology for Full Monolithic MOSFET and JBS Vertical Integration in Multi-Terminal 4H-SiC Power Converters -- Comparing 4H-SiC NPN Buffer Layers by Epitaxial Growth and Implantation for Neural Interface Isolation -- Modeling the Charging of Gate Oxide under High Electric Field -- Complementary Two Dimensional Carrier Profiles of 4H-SiC MOSFETs by Scanning Spreading Resistance Microscopy and Scanning Capacitance Microscopy -- Temperature Dependence of 4H-SiC Gate Oxide Breakdown and C-V Properties from Room Temperature to 500 °C -- Detection of Very Fast Interface Traps at 4H-SiC/AlN and 4H-SiC/Al ₂ O ₃ Interfaces -- A Voltage Adjustable Diode Integrated SiC Trench MOSFET with Barrier Control Gate -- Effects of High Gate Voltage Stress on Threshold Voltage Stability in Planar and Trench SiC Power MOSFETs -- Design of Al ₂ O ₃ /LaAlO ₃ /SiO ₂ Gate Stack on Various Channel Planes for High-

Performance 4H-SiC Trench Power MOSFETs -- Channel Density Design
Guidelines for the Transient Characteristics of SiC Trench Gate
MOSFETs -- Analysis of On-State and Short-Circuit Capability in 3D
Trench SiC MOSFET Designs -- Revised Channel Mobility Model for
Predictive TCAD Simulations of 4H-SiC MOSFETs -- Improvement of
Reflectance Spectroscopy for Oxide Layers on 4H-SiC -- Doping and
Temperature Dependence of Carrier Lifetime in 4H SiC Epitaxial Layers.
Fail-to-Open Short Circuit Failure Mode of SiC Power MOSFETs: 2-D
Thermo-Mechanical Modeling -- Gate Resistance Integration in SiC
MOSFETs: Performance Simulations under Different Implementation
Methods -- Fast Estimation of the Lateral Fidelity of Ion Implantation in
4H-SiC through Calibration to JFET Transfer Characteristics in TCAD --
Keyword Index -- Author Index.

Sommario/riassunto

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